

SEMiX302KT16s



SEMiX[®] 2s

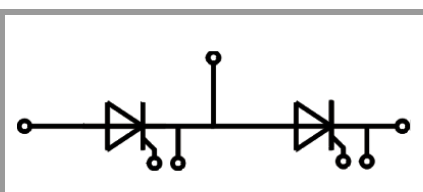
Rectifier Thyristor Module SEMiX302KT16s

Features

- Terminal height 17 mm
- Chips soldered directly to isolated substrate

Typical Applications*

- Input Bridge Rectifier for AC/DC motor control
- Power supply



KT

Absolute Maximum Ratings				
Symbol	Conditions		Values	Unit
Chip				
$I_{T(AV)}$	sinus 180°	$T_c = 85\text{ °C}$	300	A
		$T_c = 100\text{ °C}$	230	A
I_{TSM}	10 ms	$T_j = 25\text{ °C}$	9300	A
		$T_j = 130\text{ °C}$	8000	A
i^2t	10 ms	$T_j = 25\text{ °C}$	432000	A ² s
		$T_j = 130\text{ °C}$	320000	A ² s
V_{RSM}			1700	V
V_{RRM}			1600	V
V_{DRM}			1600	V
$(di/dt)_{cr}$	$T_j = 130\text{ °C}$		130	A/μs
$(dv/dt)_{cr}$	$T_j = 130\text{ °C}$		1000	V/μs
T_j			-40 ... 130	°C
Module				
T_{stg}			-40 ... 125	°C
V_{isol}	AC sinus 50Hz	1 min	4000	V
		1 s	4800	V

Characteristics						
Symbol	Conditions		min.	typ.	max.	Unit
Chip						
V_T	$T_j = 25\text{ °C}, I_T = 900\text{ A}$				1.7	V
$V_{T(TO)}$	$T_j = 130\text{ °C}$				0.85	V
r_T	$T_j = 130\text{ °C}$				1.7	mΩ
$I_{DD}; I_{RD}$	$T_j = 130\text{ °C}, V_{DD} = V_{DRM}; V_{RD} = V_{RRM}$				75	mA
t_{gd}	$T_j = 25\text{ °C}, I_G = 1\text{ A}, di_G/dt = 1\text{ A/μs}$			1		μs
t_{gr}	$V_D = 0.67 * V_{DRM}$			2		μs
t_q	$T_j = 130\text{ °C}$			150		μs
I_H	$T_j = 25\text{ °C}$			150	500	mA
I_L	$T_j = 25\text{ °C}, R_G = 33\text{ Ω}$			300	1000	mA
V_{GT}	$T_j = 25\text{ °C}, \text{d.c.}$		3			V
I_{GT}	$T_j = 25\text{ °C}, \text{d.c.}$		200			mA
V_{GD}	$T_j = 130\text{ °C}, \text{d.c.}$				0.25	V
I_{GD}	$T_j = 130\text{ °C}, \text{d.c.}$				10	mA
$R_{th(j-c)}$	continuous DC	per thyristor				K/W
		per module				K/W
$R_{th(j-c)}$	sin. 180°	per thyristor			0.091	K/W
		per module				K/W
$R_{th(j-c)}$		per thyristor				K/W
		per module				K/W
Module						
$R_{th(c-s)}$	per chip					K/W
	per module			0.045		K/W
M_s	to heat sink (M5)		3		5	Nm
M_t	to terminals (M6)		2.5		5	Nm
a					5 * 9,81	m/s ²
w				250		g

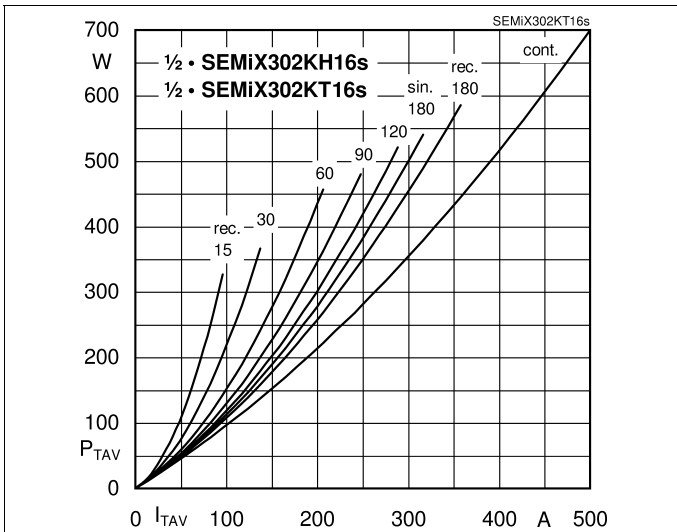


Fig. 1L: Power dissipation per thyristor/diode vs. on-state current

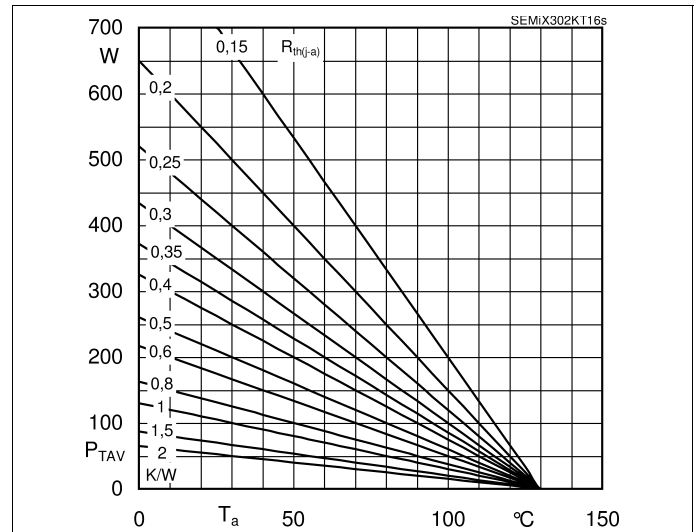


Fig. 1R: Power dissipation per thyristor/diode vs. ambient temperature

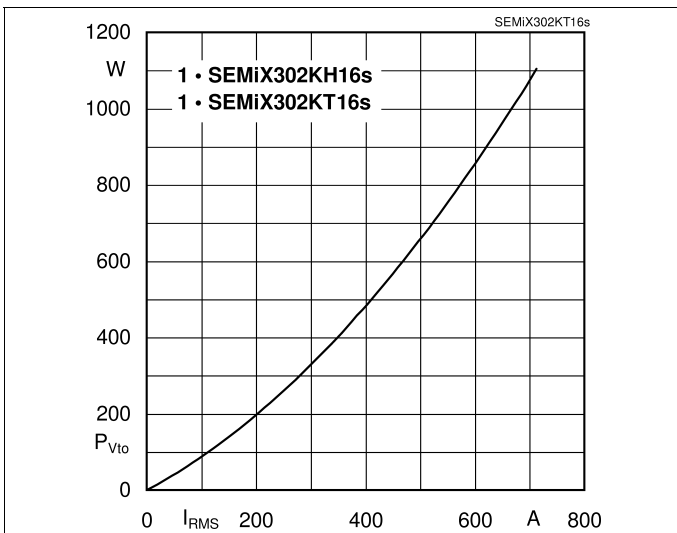


Fig. 2L: Power dissipation of one module vs. rms current

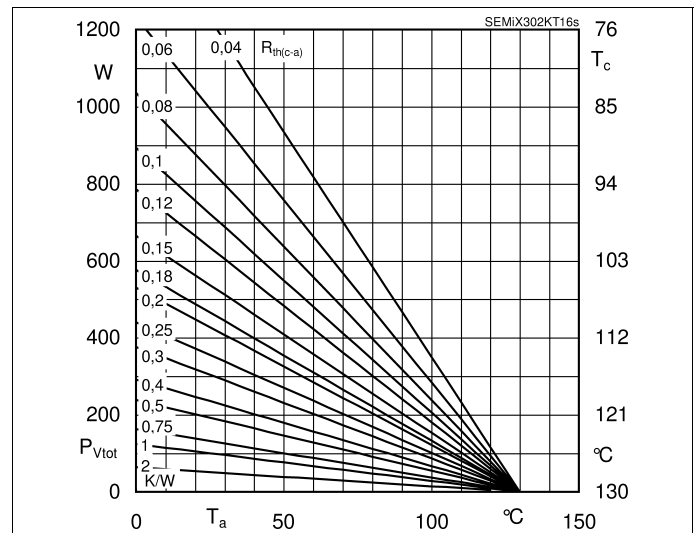


Fig. 2R: Power dissipation of one module vs. case temperature

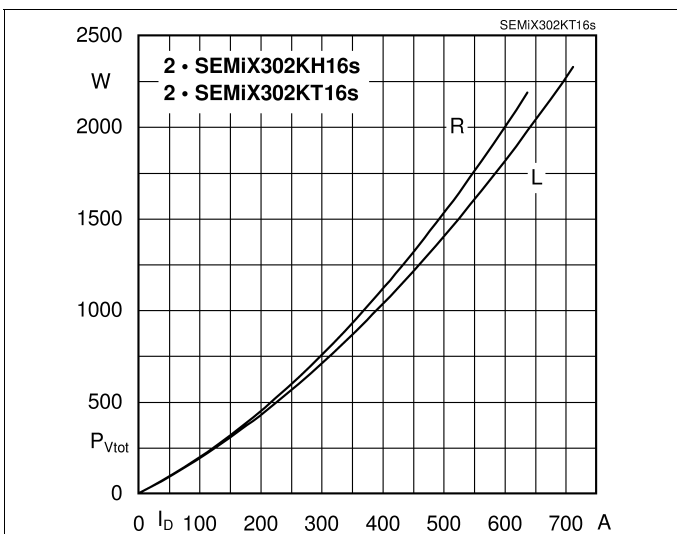


Fig. 3L: Power dissipation of two modules vs. direct current

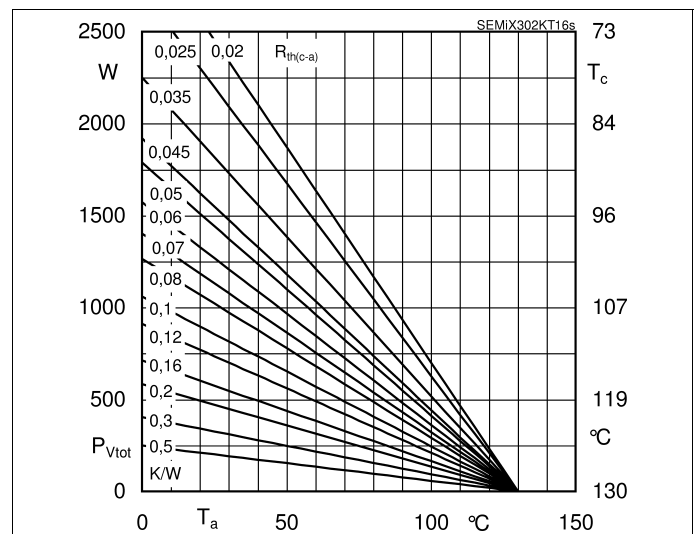


Fig. 3R: Power dissipation of two modules vs. case temperature

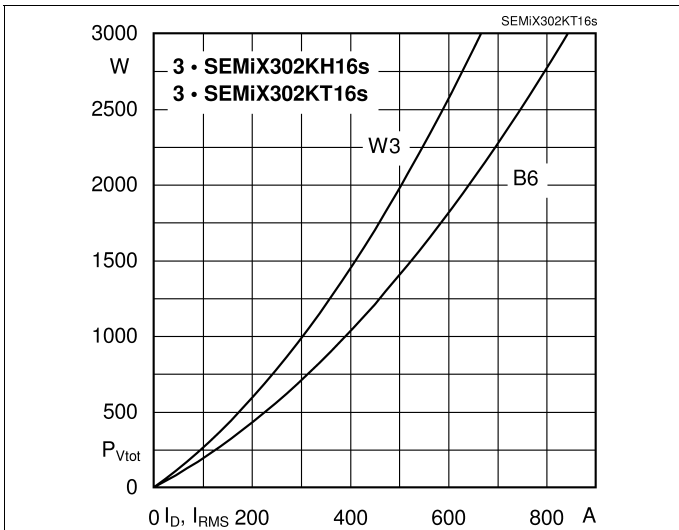


Fig. 4L: Power dissipation of three modules vs. direct current

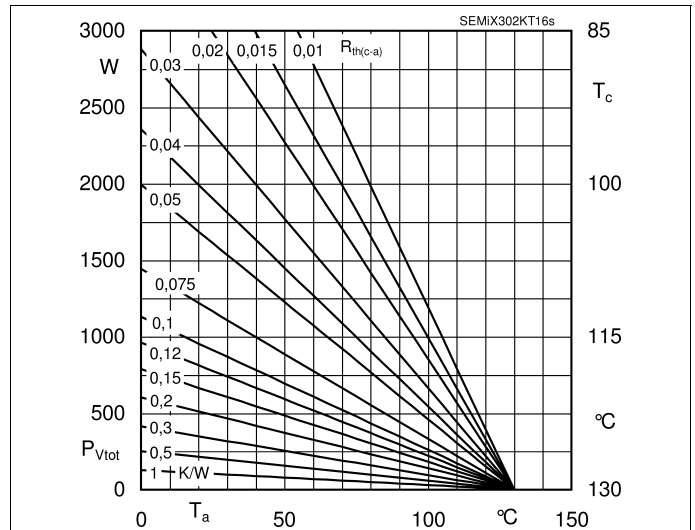


Fig. 4R: Power dissipation of three modules vs. case temperature

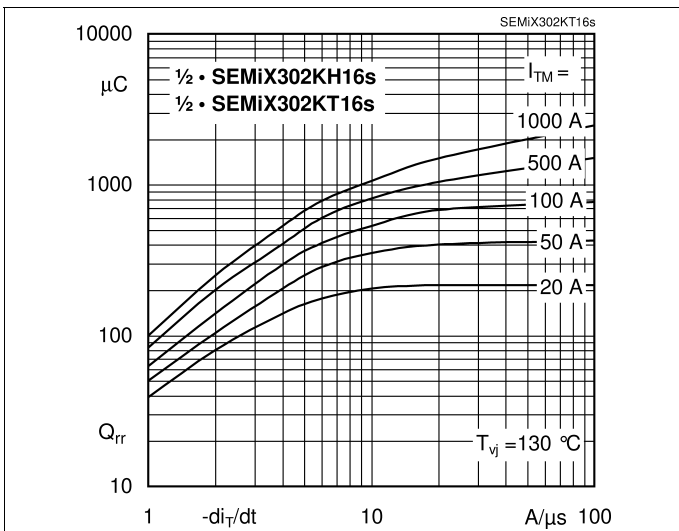


Fig. 5: Recovered charge vs. current decrease

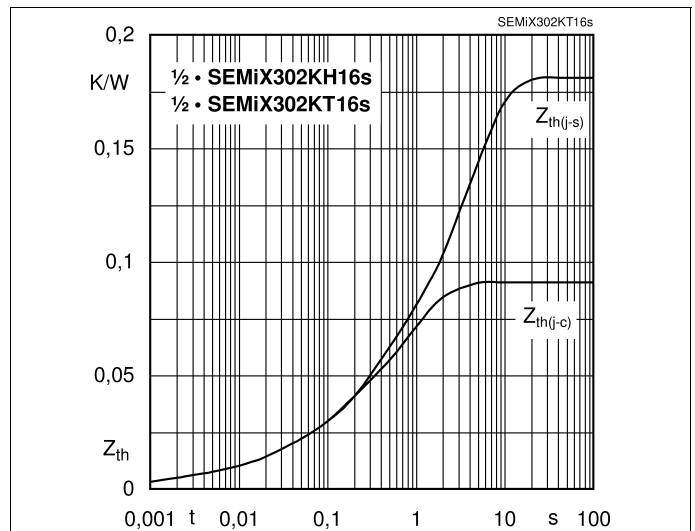


Fig. 6: Transient thermal impedance vs. time

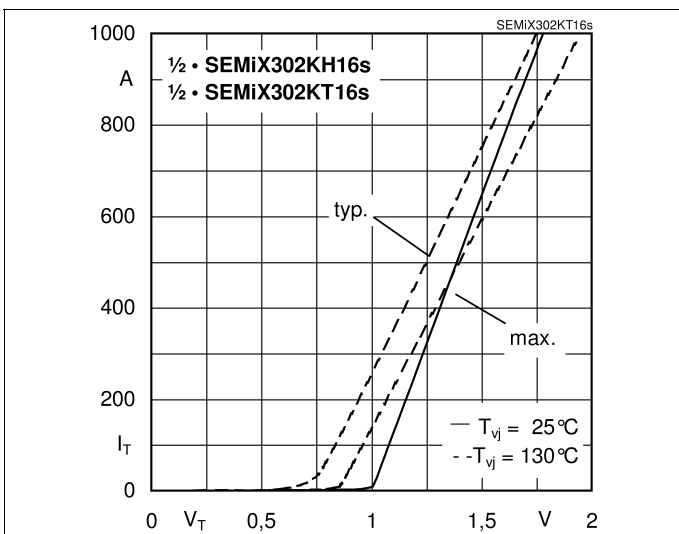


Fig. 7: On-state characteristics

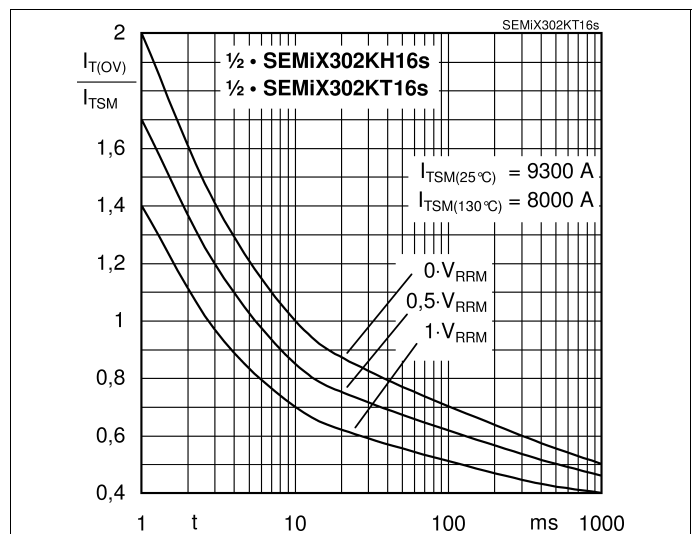


Fig. 8: Surge overload current vs. time

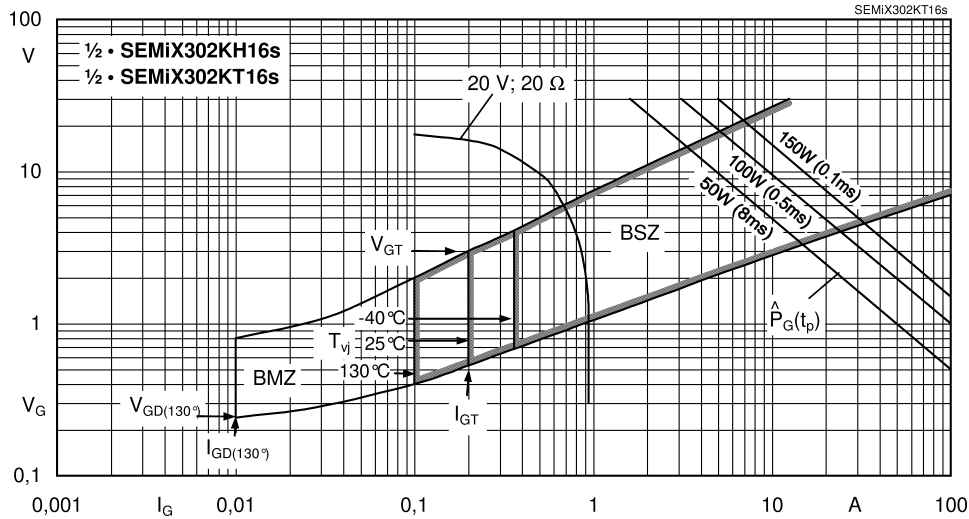
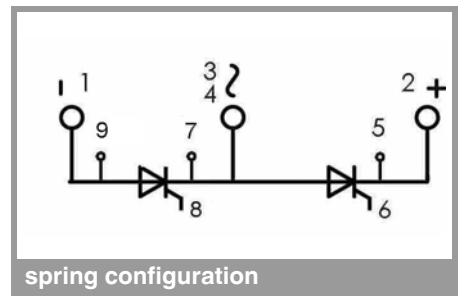
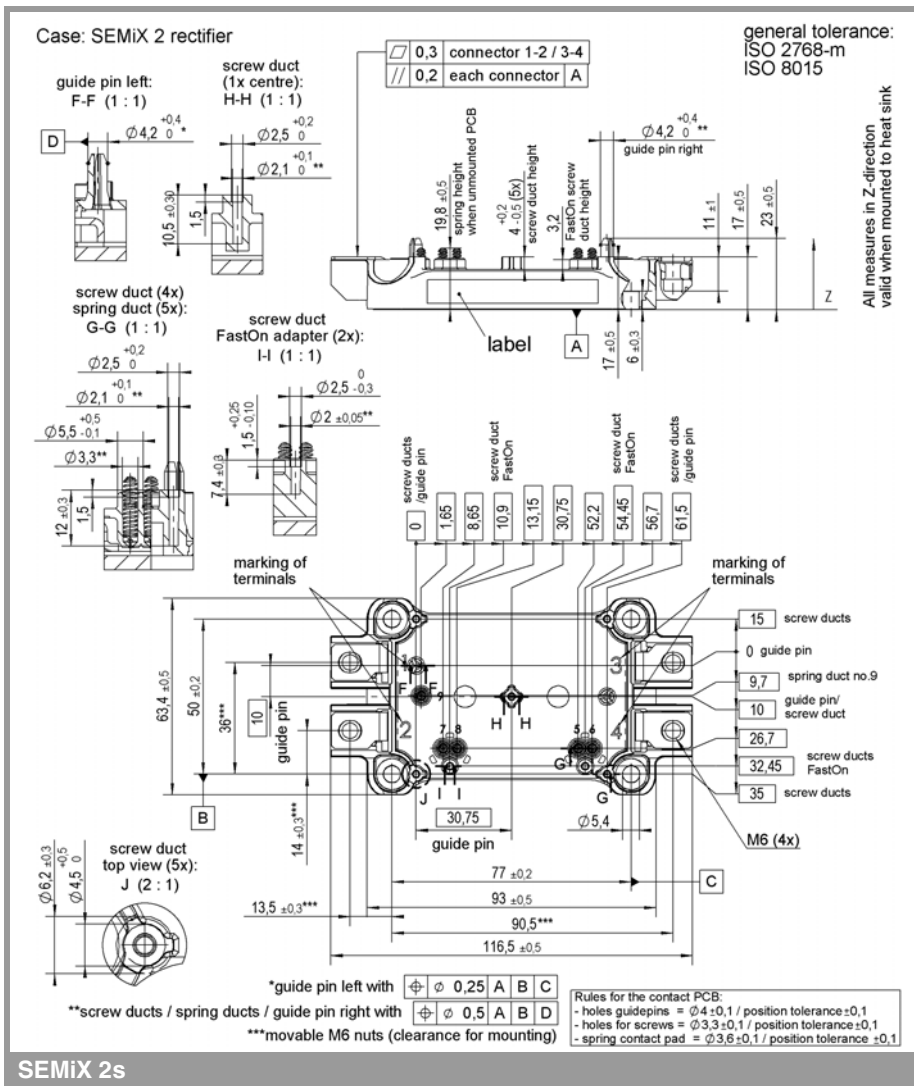


Fig. 9: Gate trigger characteristics



This is an electrostatic discharge sensitive device (ESDS), international standard IEC 60747-1, Chapter IX

* The specifications of our components may not be considered as an assurance of component characteristics. Components have to be tested for the respective application. Adjustments may be necessary. The use of SEMIKRON products in life support appliances and systems is subject to prior specification and written approval by SEMIKRON. We therefore strongly recommend prior consultation of our staff.